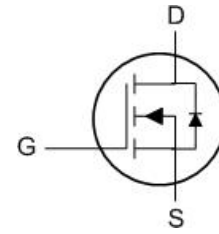




- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

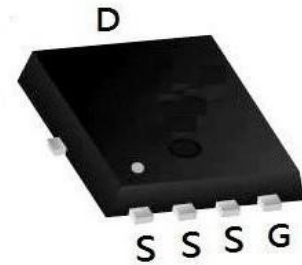


Description

The WLQ80N03BF is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WLQ80N03BF meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN5060-8L Pin Configuration



Product Summary

BVDSS	RDSON	ID
30V	3.2mΩ	80A

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	±20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80		A
$I_D@T_C=75^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	45		A
I_{DM}	Pulsed Drain Current ²	290		A
EAS	Single Pulse Avalanche Energy ³	196		mJ
I_{AS}	Avalanche Current	36		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	46		W
T_{STG}	Storage Temperature Range	-55 to 175		°C
T_J	Operating Junction Temperature Range	-55 to 175		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.72	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =30A	---	3.2	4.5	mΩ
		V _{GS} =4.5V, I _D =15A	---	4.8	8.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =30V, V _{GS} =0V, T _J =100°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =30A	---	80	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2	---	Ω
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _D =30A	---	20	---	nC
Q _{gs}	Gate-Source Charge		---	5	---	
Q _{gd}	Gate-Drain Charge		---	7.2	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DD} =15V, R _G =3Ω, I _D =30A	---	9	---	ns
T _r	Rise Time		---	16	---	
T _{d(off)}	Turn-Off Delay Time		---	43	---	
T _f	Fall Time		---	12	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	2088	---	pF
C _{oss}	Output Capacitance		---	277	---	
C _{rss}	Reverse Transfer Capacitance		---	209	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	80	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

F¹ The data is tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

G² The data is tested by pulsed pulse width ≤ 300us, duty cycle ≤ 2%

H³ The EAS data shows Max. Rating. The test condition is V_{RM} > 0, V_{DD}=24V, V_{GS}=10V, L=0.1mH, I_{AS}=36A.

I⁴ The power dissipation is limited by 150°C junction temperature

J⁵ The data is theoretically the same as A₀ and A_{DMA}. In real applications it should be limited by total power dissipation.



Typical Electrical and Thermal Characteristics (Curves)

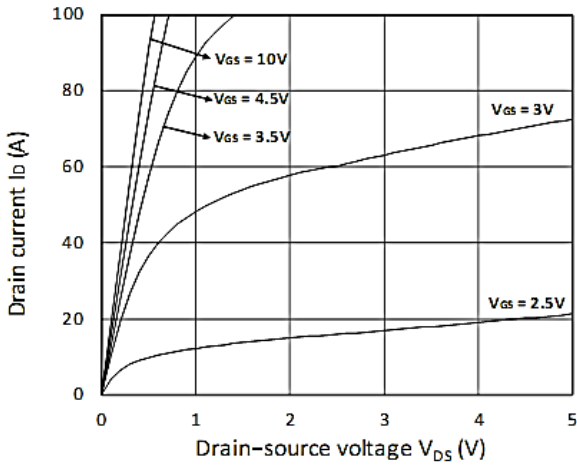


Figure 1. Output Characteristics

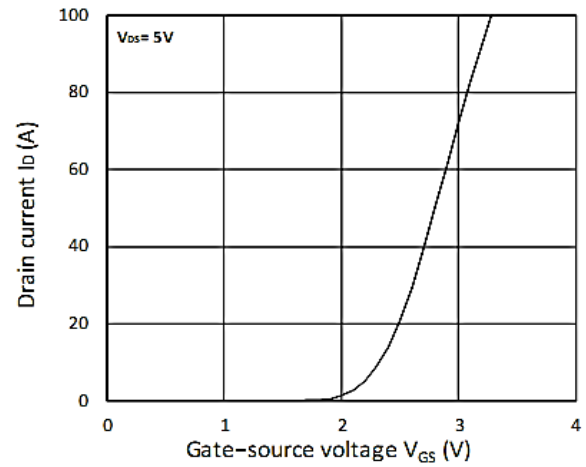


Figure 2. Transfer Characteristics

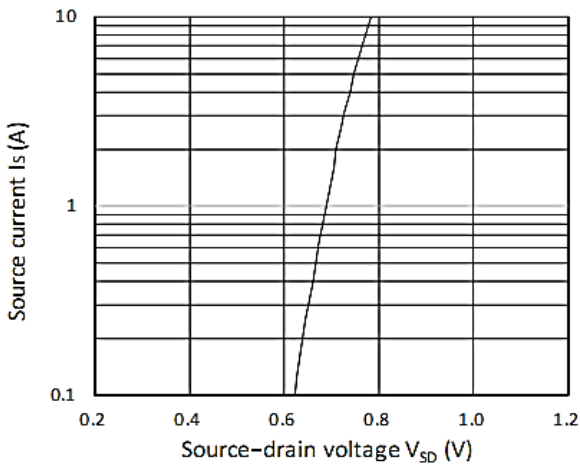


Figure 3. Forward Characteristics of Reverse

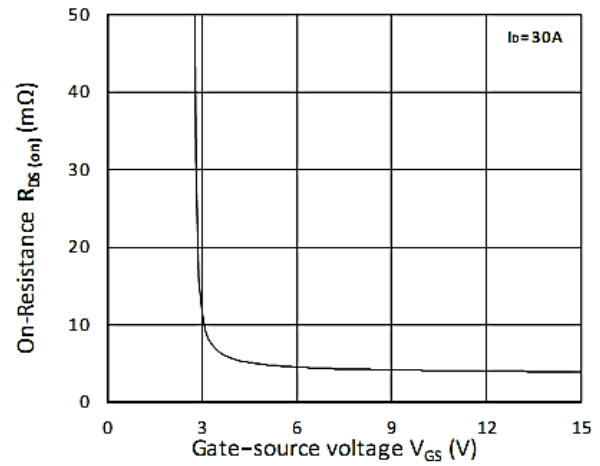


Figure 4. R_DS(ON) vs. V_GS

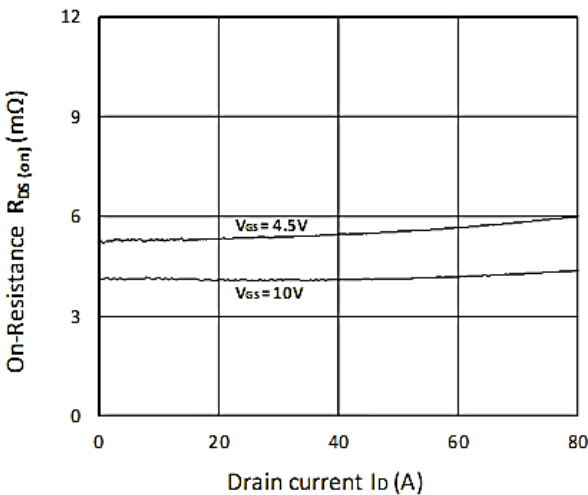


Figure 5. R_DS(ON) vs. I_D

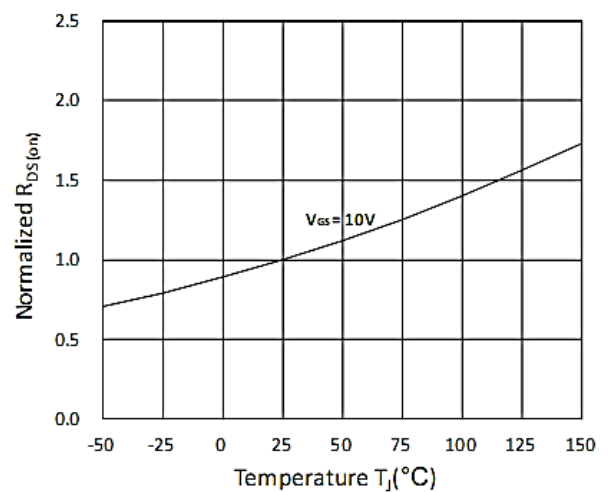


Figure 6. Normalized R_DS(on) vs. Temperature

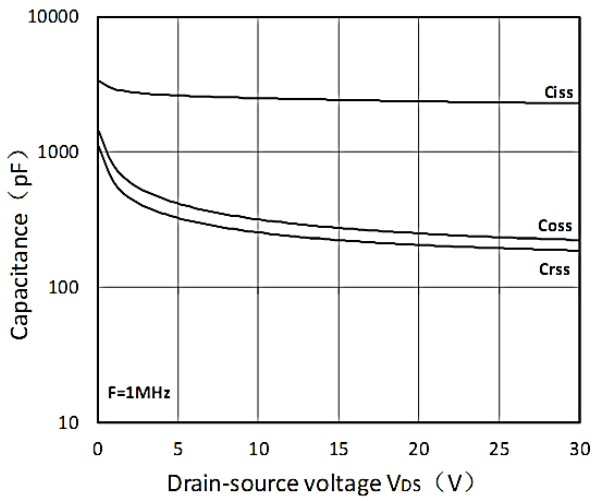


Figure 7. Capacitance Characteristics

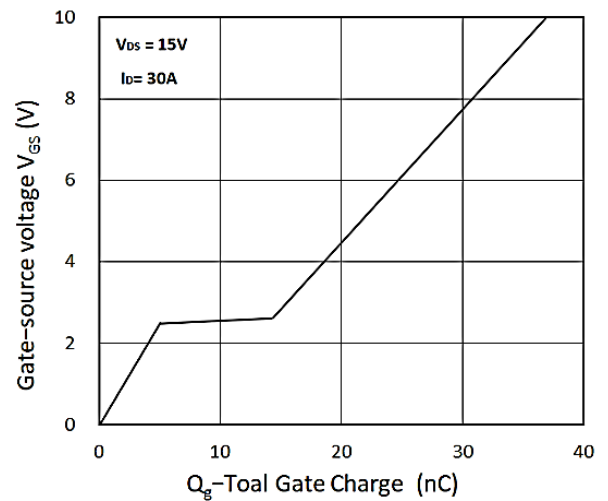


Figure 8. Gate Charge Characteristics

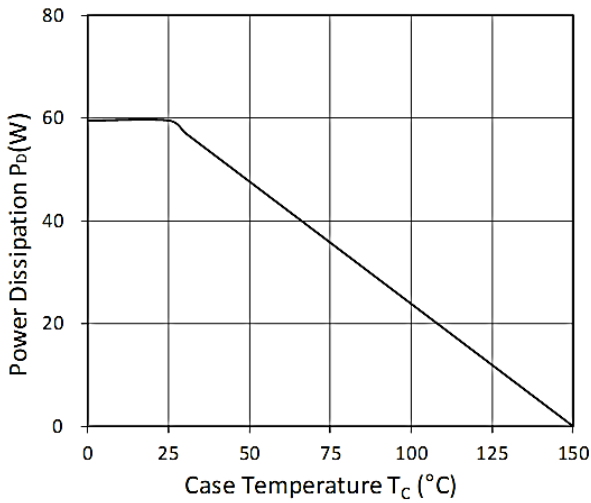


Figure 9. Power Dissipation

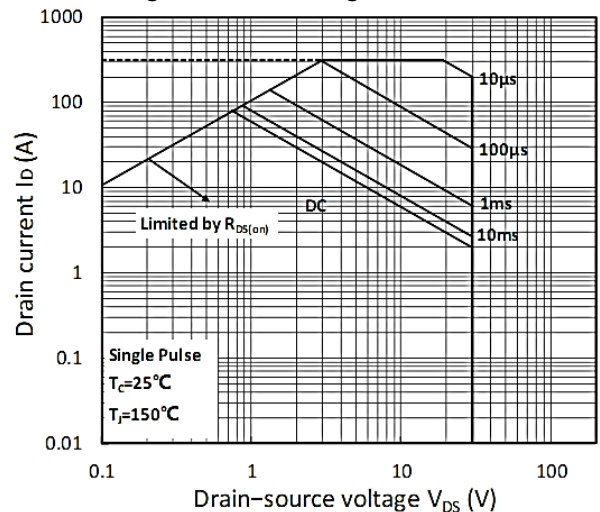


Figure 10. Safe Operating Area

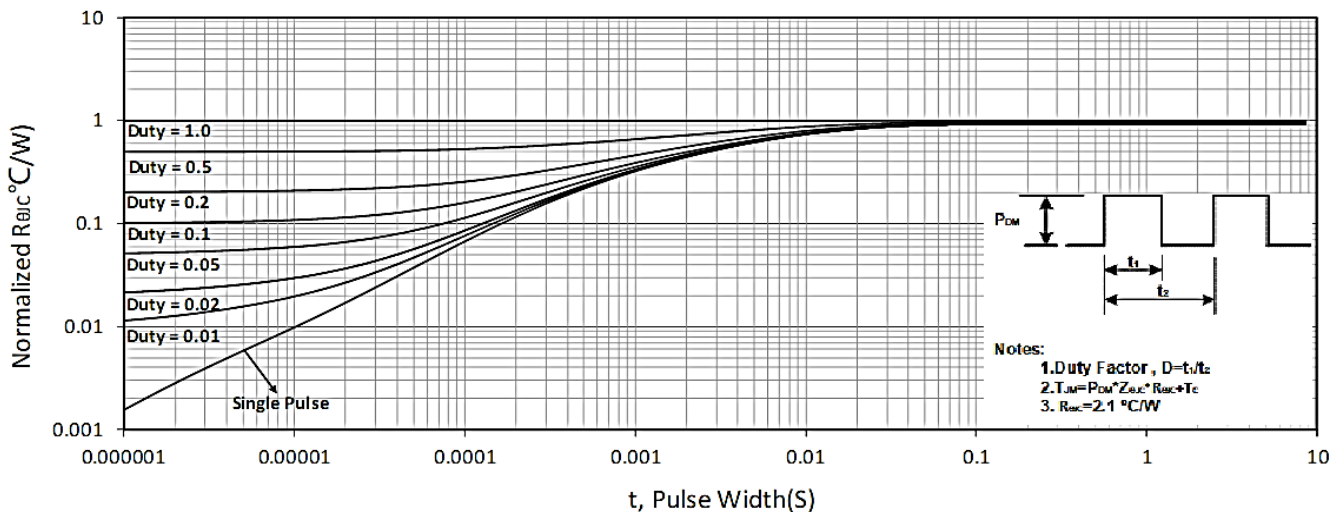
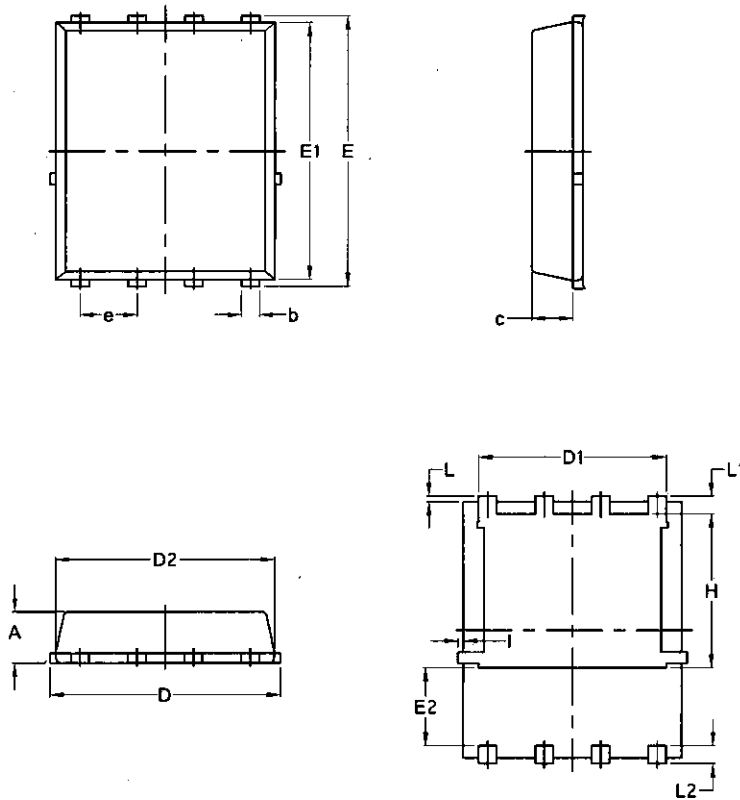


Figure 11. Normalized Maximum Transient Thermal Impedance



Package Mechanical Data-PDFN5060-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070



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